

FEATURES

- n **HIGH POWER**
P1dB=34.5dBm at 13.75GHz to 14.5GHz
- n **HIGH GAIN**
G1dB=26.0dB at 13.75GHz to 14.5GHz
- n **BROAD BAND INTERNALLY MATCHED**
- n **HERMETICALLY SEALED PACKAGE**

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	10
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	20
Flange Temperature	Tf	°C	-40 ~ +90
Storage Temperature	Tstg	°C	-65 ~ +175

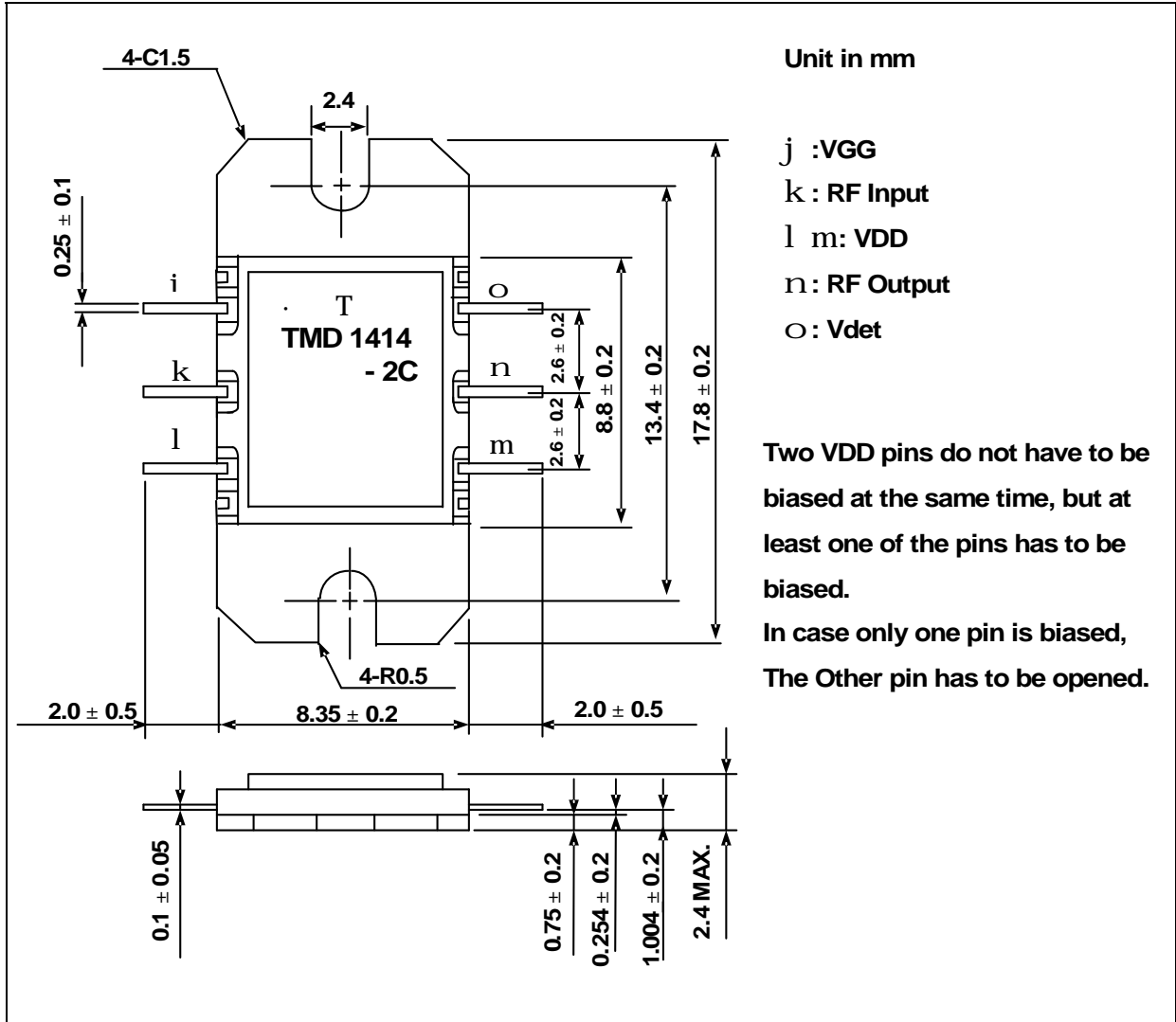
RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Operating Frequency	f		GHz	13.75	—	14.5
Output Power at 1dB Gain Compression Point	P1dB	VDD=7V VGG=-5V	dBm	32.0	34.5	—
1dB Gain Compression Point	G1dB		dB	21.0	26.0	—
Gain Flatness	ΔG		dB	—	—	±1.0
Drain Current	IDD		A	—	1.4	1.8
Power Added Efficiency	hadd		%	—	29	—

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PACKAGE OUTLINE (7-BA15A)



Recommended Bias Configuration

